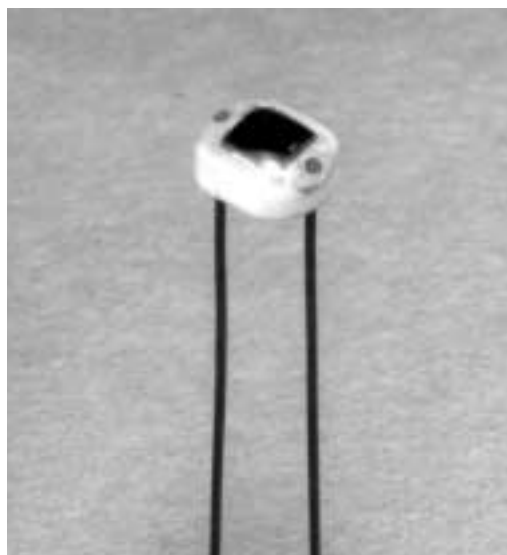
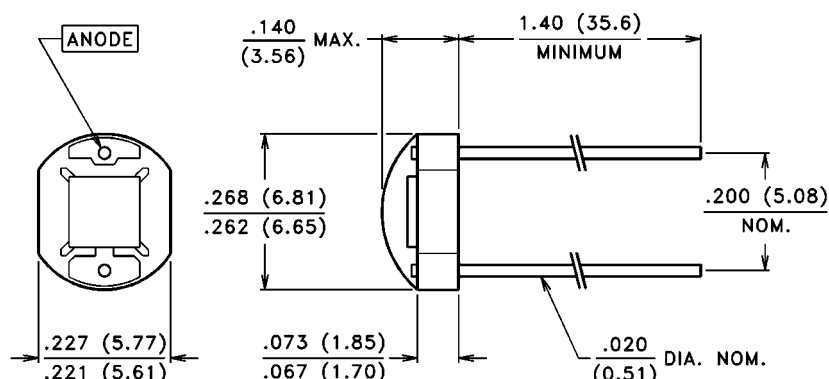




PACKAGE DIMENSIONS inch (mm)



CASE 11 CERAMIC
CHIP ACTIVE AREA: .008 in² (5.16 mm²)

PRODUCT DESCRIPTION

Planar silicon photodiode mounted on a two lead ceramic substrate and coated with a thick layer of clear epoxy. These diodes have very high shunt resistance and have good blue response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C
Operating Temperature: -20°C to 75°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB8341			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	35	60		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.12	.23	%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		490		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 2.0 V			100	pA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		1.4		GΩ
TC R _{SH}	R _{SH} Temperature Coefficient	H = 0, V = 10 mV		-8.0		%/°C
C _J	Junction Capacitance	H = 0, V = 0		1.0		nF
S _R	Sensitivity	365 nm		.10		A/W
λ _{range}	Spectral Application Range		320		1100	nm
λ _p	Spectral Response - Peak			920		nm
V _{BR}	Breakdown Voltage		2	40		V
θ _{1/2}	Angular Resp. - 50% Resp. Pt.			±60		Degrees
NEP	Noise Equivalent Power		2.4 x 10 ⁻¹⁴ (Typ.)			W/√Hz
D*	Specific Detectivity		9.7 x 10 ¹² (Typ.)			cm√Hz / W